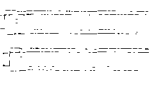
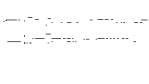
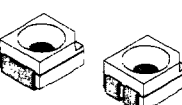
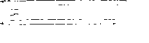
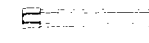
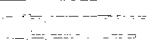


Detectors

Photo Transistors

Package	Type	Photo Sensitive Area/mm ²	± φ	Characteristics				
				I _{ca} / mA @ E _c / mW / cm ² (V _{CE} = 5 V, λ = 950 nm)	t _r / μs @ I _C = 5 mA, λ = 950 nm	R _L / kΩ		
Photo Transistors in Clear Plastic Package								
	BPW16N	0.36	40°	0.14(>0.07)	1	3.7	0.1	
	BPW17N		12.5°	1.0(>0.5)				
	BPW85A	0.18	25°	0.8–2.5	1	1.5	0.1	
	BPW85B			1.5–4.0				
	BPW85C			3.0–8.0				
	BPW96A	0.18	20°	1.5–4.5	1	1.5	0.1	
	BPW96B			2.5–7.5				
	BPW96C			4.5–15				
	BPV11	0.36	15°	10(>3)		3.8		
SMD Photo Transistors in Clear Plastic Package								
	TEMT2100	0.18	70°	0.45(>0.3)	1	1.5	0.1	
	TEMT3700 TEMT4700 ¹⁾	0.07		0.5(>0.2)		5	1	
Photo Transistors with Filter Matched for GaAs IREDs in Plastic Package								
	S350P	0.36	40°	1(>0.2)	1	3.8	0.1	
	BPW78A		25°	1.0–3.0				
	BPW78B			4(>2.0)				
	TEFT4300	0.18	30°	3.2(>0.8)	1	1.5	0.1	
	TEST2600	0.36	30°/60°	2.5(>1.0)		3.8		
	BPV11F		15°	9(>3.0)				
Photo Darlington with Filter Matched for GaAs IREDs in Plastic Package								
	S289P	0.21	30°	15(>4.0)	0.3	80	0.1	

¹⁾ with base connection